

Usha C

List of Publications by Year in descending order

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11
papers

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2258059

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citing authors

#	ARTICLE	IF	CITATIONS
1	Electrostatic characteristics of a high-k stacked gate-all-around heterojunction tunnel field-effect transistor using the superposition principle. <i>Journal of Computational Electronics</i> , 2022, 21, 181-190.	2.5	5
2	Modeling of Source Pocket Engineered PNP Tunnel FET on High-K Buried Oxide (H-BOX) Substrate for Improved ON Current. <i>Silicon</i> , 2022, 14, 10383-10389.	3.3	3
3	A new analytical approach to threshold voltage modeling of triple material gate-all-around heterojunction tunnel field effect transistor. <i>Indian Journal of Physics</i> , 2021, 95, 1365-1371.	1.8	8
4	An Analytical Modeling of Conical Gate-All-Around Tunnel Field Effect Transistor. <i>Silicon</i> , 2021, 13, 2563-2568.	3.3	4
5	Physics based model for potential distribution and threshold voltage of gate-all-around tunnel field effect transistor (GAA-TFET). <i>Materials Today: Proceedings</i> , 2021, 45, 4052-4057.	1.8	1
6	Impact Analysis and Simulation of Cylindrical Nanowire Biosensor. , 2021, , .		1
7	Analytical Drain Current Modeling and Simulation of Triple Material Gate-All-Around Heterojunction TFETs Considering Depletion Regions. <i>Semiconductors</i> , 2020, 54, 1634-1640.	0.5	3
8	A novel 2-D analytical model for the electrical characteristics of a gate-all-around heterojunction tunnel field-effect transistor including depletion regions. <i>Journal of Computational Electronics</i> , 2020, 19, 1144-1153.	2.5	11
9	A compact two-dimensional analytical model of the electrical characteristics of a triple-material double-gate tunneling FET structure. <i>Journal of Semiconductors</i> , 2019, 40, 122901.	3.7	1
10	A tunneling FET exploiting in various structures and different models: A review. , 2015, , .		7
11	Analytical Drain Current Model for Fully Depleted Surrounding Gate TFET. <i>Journal of Nano Research</i> , 0, 55, 75-81.	0.8	13